Icemos Technology Ltd Product Specification 1003.280801 Issue Date 27 September 2013 11

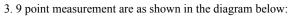
Part Number	Customer	

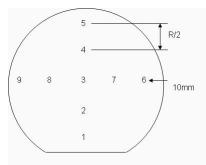
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none / semi std	wafer vendor
	5.0	Overall Thickness	384.00 +/- 27.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00um	ADE, 100% measurement
	7.0	Bow	<80.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	380.00 +/- 25.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	0.01 - 0.5 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and lasermark.	Guaranteed by process
BuriedOxide	18.0	Oxide formed on	Handle Wafer	Guaranteed by process
	19.0	Oxide Type	Thermal	Guaranteed by process
	20.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec 4%, 5pt
DeviceSilicon	21.0	Scratches	0	Bright Light, 100% (note 2)
	22.0	Haze	none	Bright Light, 100% (note 2)
	23.0	Surface	front side prime polished (before oxide and poly deposition)	Guaranteed by process
	24.0	PolySilicon	20000A +/- 1000A, doped with resistivity 0.001 ~ 0.005 Ohm cm	4 pt probe 100%

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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	ction performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information